

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	5474	(257/635,637,640,641,751,752,760,762,773,774).CCLS.	USPAT
2	IS&R	L2	3017	(257/635,637,640,641,751,752,760,762,773,774).CCLS.	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	0	((conductive metal metalization) and (diffusion barrier) and ((etch etching) near2 (stop stopping)) and (dielectric insulation insulating) and (sidewall side adj wall) and (via hole) and (reverse near2 (sputter sputtering))).clm.	US-PGPUB
4	BRS	L4	179	((conductive metal metalization) and (diffusion barrier) and ((etch etching) near2 (stop stopping)) and (dielectric insulation insulating) and (via hole)).clm.	US-PGPUB

	Time Stamp	Comments	Error Definition	Errors
1	2005/11/15 06:51			
2	2005/11/15 07:13			
3	2005/11/15 07:27			
4	2005/11/15 07:28			